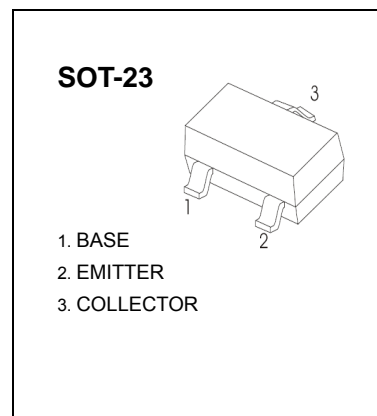


SOT-23 Plastic-Encapsulate Transistors

1SS226 SWITCHING DIODE

FEATURES

- Low forward voltage
- Fast reverse recovery time
- Small total capacitance



MARKING: C3

Maximum Ratings ,Single Diode @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	85	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	80	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	100	mA
Peak Forward Surge Current @t=10ms	I_{FSM}	2	A
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	80		V
Reverse voltage leakage current	I_R	$V_R=80V$		0.5	μA
Forward voltage	V_F	$I_F=100mA$		1.2	V
Diode capacitance	C_D	$V_R=0V, f=1MHz$		3	pF
Reverse recovery time	t_{rr}	$I_F=10mA$		4	ns

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